Transistors Panasonic

2SA2162

Silicon PNP epitaxial planar type

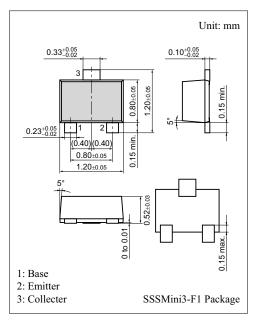
For general amplification Complementary to 2SC6036

■ Features

- ullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- SSS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|---------------------|------|--|
| Collector-base voltage (Emitter open) | V _{CBO} | -15 | V | |
| Collector-emitter voltage (Base open) | V _{CEO} | -12 | V | |
| Emitter-base voltage (Collector open) | V _{EBO} | V _{EBO} –5 | | |
| Collector current | I_{C} | -500 | mA | |
| Peak collector current | I _{CP} | -1 | A | |
| Collector power dissipation | P _C | 100 | mW | |
| Junction temperature | T_{j} | 125 | °C | |
| Storage temperature | T _{stg} | -55 to +125 | °C | |



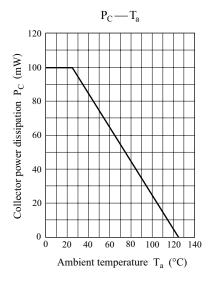
Marking Symbol: 2U

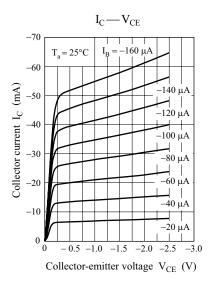
■ Electrical Characteristics $T_a = 25$ °C±3°C

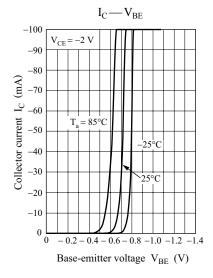
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|---|-----|-----|------|------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_{\rm C} = -10 \mu\text{A}, I_{\rm E} = 0$ | -15 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = -1 \text{ mA}, I_{\rm B} = 0$ | -12 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = -10 \mu A, I_C = 0$ | -5 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{\rm CB} = -10 \text{V}, I_{\rm E} = 0$ | | | -0.1 | μΑ |
| Forward current transfer ratio | h_{FE} | $V_{CE} = -2 \text{ V}, I_{C} = -10 \text{ mA}$ | 270 | | 680 | _ |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = -200 \text{ mA}, I_B = -10 \text{ mA}$ | | | -250 | mV |
| Transition frequency | f_T | $V_{CB} = -2 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$ | | 200 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C _{ob} | $V_{CB} = -10 \text{ V, f} = 1 \text{ MHz}$ | | 4.5 | | pF |

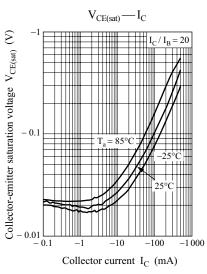
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

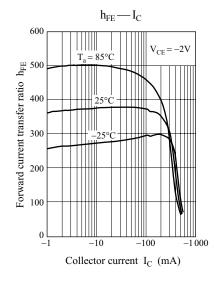
2SA2162 Panasonic

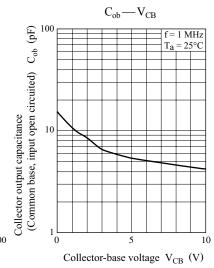












2 SJC00323AED

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